

Amendments to the Specification:

Please replace the abstract at page 19 with the following amended abstract:

--A junction field-effect transistor (~~20~~) comprises an n-type semiconductor layer (~~1~~) having a channel region, a buffer layer (~~3~~) formed on the channel region and a p<sup>+</sup> region (~~4a, 4b~~) formed on the buffer layer (~~3~~). The concentration of electrons in the buffer layer (~~3~~) is lower than the concentration of electrons in the semiconductor layer (~~1~~). The concentration of electrons in the buffer layer (~~3~~) is preferably not more than one tenth of the concentration of electrons in the semiconductor layer (~~1~~). Thus, the threshold voltage can be easily controlled, and saturation current density of a channel can be easily controlled.--